## Abdelouahad El Fatimy

List of Publications by Year in descending order

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| # | Article   | IF        | CITATIONS    |
|---|---|-----------|--------------|
| 1 | Phosphorene—an emerging two-dimensional material: recent advances in synthesis, functionalization, and applications. 2D Materials, 2022, 9, 032001.   | 4.4       | 25           |
| 2 | Adjustment of Terahertz Properties Assigned to the First Lowest Transition of (D+, X) Excitonic<br>Complex in a Single Spherical Quantum Dot Using Temperature and Pressure. Applied Sciences<br>(Switzerland), 2021, 11, 5969. | 2.5       | 4            |
| 3 | Nanostructured graphene for nanoscale electron paramagnetic resonance spectroscopy. JPhys<br>Materials, 2020, 3, 014013.  | 4.2       | 11           |
| 4 | Effect of defect-induced cooling on graphene hot-electron bolometers. Carbon, 2019, 154, 497-502.   | 10.3      | 15           |
| 5 | Ambient effects on photogating in MoS <sub>2</sub> photodetectors. Nanotechnology, 2019, 30, 284004.  | 2.6       | 36           |
| 6 | Ultra-broadband photodetectors based on epitaxial graphene quantum dots. Nanophotonics, 2018, 7,<br>735-740.  | 6.0       | 28           |
| 7 | Highly sensitive MoS <sub>2</sub> photodetectors with graphene contacts. Nanotechnology, 2018, 29, 20LT01.  | 2.6       | 38           |
| 8 | Nanostructured epitaxial graphene for ultra-broadband optoelectronic detectors (Conference) Tj ETQq0 0 0 rgBT   | /Overlock | 18 Tf 50 462 |
| 0 | Epitaxial graphene quantum dots for high-performance terahertz bolometers. Nature   | 01.5      | 117          |

| 9  | Nanotechnology, 2016, 11, 335-338.   | 31.5 | 116 |
|----|--|------|-----|
| 10 | Nanotransistor based THz plasma detectors: low tempeatures, graphene, linearity, and circular polarization studies. , 2013, , .                    |      | 2   |
| 11 | Temperature, back gate and polarization studies in nanotransistor based THz plasma detectors. , 2013, ,  |      | 0   |
| 12 | Field Effect Transistors for Terahertz Detection and Emission. Journal of Infrared, Millimeter, and<br>Terahertz Waves, 2011, 32, 618-628.         | 2.2  | 40  |
| 13 | Terahertz detection by field effect transistors security imaging. Proceedings of SPIE, 2011, , .   | 0.8  | 0   |
| 14 | THz Emission Related to Hot Plasmons and Plasma Wave Instability in Field Effect Transistors. Acta<br>Physica Polonica A, 2011, 120, 924-926.      | 0.5  | 2   |
| 15 | Terahertz Detection of Quantum Cascade Laser Emission by Plasma Waves in Field Effect Transistors.<br>Acta Physica Polonica A, 2011, 120, 930-932. | 0.5  | 1   |
| 16 | Plasma excitations in field effect transistors for terahertz detection and emission. Comptes Rendus<br>Physique, 2010, 11, 433-443.                | 0.9  | 12  |
| 17 | Tunable room temperature THz emission from AlGaN/GaN high electron mobility transistors. , 2010, , .   |      | 0   |
| 18 | THz communication system based on a THz Quantum Cascade Laser and a Hot Electron Bolometer. , 2010, , .  |      | 2   |

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|----|---|-----|-----------|
| 19 | AlGaN/GaN high electron mobility transistors as a voltage-tunable room temperature terahertz<br>sources. Journal of Applied Physics, 2010, 107, .   | 2.5 | 133       |
| 20 | Room temperature Terahertz hot electron bolometric detector based on AlGaAs/GaAs two dimensional electron gas. , 2010, , .  |     | 0         |
| 21 | Field Effect Transistors for Terahertz Detection: Physics and First Imaging Applications. Journal of<br>Infrared, Millimeter, and Terahertz Waves, 2009, 30, 1319.  | 2.2 | 199       |
| 22 | Field effect transistors for terahertz imaging. Physica Status Solidi C: Current Topics in Solid State<br>Physics, 2009, 6, 2828-2833.  | 0.8 | 9         |
| 23 | Broadband terahertz imaging of documents written with lead pencils. Optics Communications, 2009, 282, 3104-3107.  | 2.1 | 54        |
| 24 | Plasma wave field effect transistor as a resonant detector for 1 terahertz imaging applications. Optics Communications, 2009, 282, 3055-3058.   | 2.1 | 28        |
| 25 | Terahertz plasmon-resonant microship emitters and their possible sensing and spectroscopic applications. , 2009, , .  |     | 2         |
| 26 | Application of plasmon-resonant microchip emitters to broadband terahertz spectroscopic measurement. Journal of the Optical Society of America B: Optical Physics, 2009, 26, A52.   | 2.1 | 21        |
| 27 | Tunable room temperature terahertz sources based on two dimensional plasma instability in GaN<br>HEMTs. Journal of Physics: Conference Series, 2009, 193, 012072.   | 0.4 | 2         |
| 28 | Plasmon-resonant Microchip Emitters and Their Applications to Terahertz Spectroscopy. Progress in<br>Electromagnetics Research Symposium: [proceedings] Progress in Electromagnetics Research<br>Symposium, 2009, 5, 341-345. | 0.4 | 0         |
| 29 | Plasma oscillations in nanotransistors for room temperature detection and emission of terahertz radiation. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 244-248.                                  | 0.8 | 13        |
| 30 | Nitride based nanotransistors as new sources and detectors of THz radiations. Physica Status Solidi<br>C: Current Topics in Solid State Physics, 2008, 5, 1947-1949.  | 0.8 | 1         |
| 31 | Terahertz imaging with GaAs field-effect transistors. Electronics Letters, 2008, 44, 408.   | 1.0 | 54        |
| 32 | Broadening of the plasmon resonance due to plasmon-plasmon intermode scattering in terahertz<br>high-electron-mobility transistors. Applied Physics Letters, 2008, 93, .  | 3.3 | 27        |
| 33 | Plasmon-plasmon scattering in two-dimensional electron channel of a terahertz nanotransistor. , 2008, , .   |     | Ο         |
| 34 | Room temperature terahertz imaging by a GaAs-HEMT transistor associated with a THz time domain spectrometer. , 2008, , .  |     | 0         |
| 35 | Terahertz Emission from Collapsing Field Domains during Switching of a Gallium Arsenide Bipolar<br>Transistor. Physical Review Letters, 2007, 99, 176601.   | 7.8 | 30        |
| 36 | Room temperature detection and emission of Terahertz radiation by plasma oscillations in nanometer size transistors. , 2007, , .  |     | 3         |

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|----|--|-----|-----------|
| 37 | Plasma wave resonant detection of terahertz radiations by nanometric transistors. Low Temperature Physics, 2007, 33, 291-294.  | 0.6 | 14        |
| 38 | Room temperature tunable detection of subterahertz radiation by plasma waves in nanometer InGaAs transistors. Applied Physics Letters, 2006, 89, 222109.             | 3.3 | 67        |
| 39 | Resonant and voltage-tunable terahertz detection in InGaAsâ^•InP nanometer transistors. Applied Physics<br>Letters, 2006, 89, 131926.                                | 3.3 | 192       |
| 40 | Plasma Wave HEMTs for THz applications. , 2006, , .  |     | 0         |
| 41 | Terahertz detection by GaN/AlGaN transistors. Electronics Letters, 2006, 42, 1342.   | 1.0 | 96        |
| 42 | Electron mobility in quasi-ballistic Si MOSFETs. Solid-State Electronics, 2006, 50, 632-636.   | 1.4 | 24        |
| 43 | Room-temperature terahertz emission from nanometer field-effect transistors. Applied Physics<br>Letters, 2006, 88, 141906.   | 3.3 | 122       |
| 44 | Room-temperature terahertz emission from nanometer field-effect transistors. , 2006, , .   |     | 2         |
| 45 | Terahertz Detection Related to Plasma Excitations in Nanometer Gate Length Field Effect Transistor<br>Materials Research Society Symposia Proceedings, 2006, 958, 1. | 0.1 | 0         |
| 46 | Terahertz Emission and Detection by Plasma Waves in Nanometer Size Field Effect Transistors. IEICE<br>Transactions on Electronics, 2006, E89-C, 926-930.             | 0.6 | 2         |
| 47 | Ballistic and pocket limitations of mobility in nanometer Si metal-oxide semiconductor field-effect transistors. Applied Physics Letters, 2005, 87, 053507.          | 3.3 | 44        |
| 48 | Influence of ballistic and pocket effects on electron mobility in si MOSFETs. , 0, , .   |     | 2         |